FEATURES

1.5 W output with THD + N < 1%
Differential bridge-tied load output
Single-supply operation: 2.7 V to 5.5 V
Functions down to 1.75 V
Wide bandwidth: 4 MHz
Highly stable phase margin: >80°
Low distortion: 0.2% THD + N at 1 W output
Excellent power supply rejection

APPLICATIONS

Portable computers
Personal wireless communicators
Hands-free telephones
Speaker phones
Intercoms
Musical toys and talking games

GENERAL DESCRIPTION

The SSM2211 is a high performance audio amplifier that delivers 1 W rms of low distortion audio power into a bridge-connected 8 Ω speaker load (or 1.5 W rms into a 4 Ω load).

The SSM2211 operates over a wide temperature range and is specified for single-supply voltages between 2.7 V and 5.5 V. When operating from batteries, it continues to operate down to 1.75 V. This makes the SSM2211 the best choice for unregulated applications, such as toys and games.

Featuring a 4 MHz bandwidth and distortion below 0.2% THD + N at 1 W, superior performance is delivered at higher power or lower speaker load impedance than competitive units. Furthermore, when the ambient temperature is at 25°C, THD + N < 1%, and Vs = 5 V on a four-layer PCB, the SSM2211 delivers a 1.5 W output.

The low differential dc output voltage results in negligible losses in the speaker winding and makes high value dc blocking capacitors unnecessary. The battery life is extended by using shutdown mode, which typically reduces quiescent current drain to 100 nA.

The SSM2211 is designed to operate over the −40°C to +85°C temperature range. The SSM2211 is available in 8-lead SOIC (narrow body) and LFCSP (lead frame chip scale) surface-mount packages. The advanced mechanical packaging of the LFCSP models ensures lower chip temperature and enhanced performance relative to standard packaging options.

Applications include personal portable computers, hands-free telephones and transceivers, talking toys, intercom systems, and other low voltage audio systems requiring 1 W output power.

1 Protected by U.S. Patent No. 5,519,576.
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### ELECTRICAL CHARACTERISTICS

$V_{DD} = 5.0 \text{ V}, T_A = 25^\circ\text{C}, R_L = 8 \\Omega, C_B = 0.1 \mu\text{F}, V_{CM} = V_{DD}/2$, unless otherwise noted.

**Table 1.**

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Symbol</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>GENERAL CHARACTERISTICS</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Differential Output Offset Voltage</td>
<td>$V_{OOS}$</td>
<td>$A_{VD} = 2, -40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$</td>
<td>4</td>
<td>50</td>
<td></td>
<td>mV</td>
</tr>
<tr>
<td>Output Impedance</td>
<td>$Z_{OUT}$</td>
<td></td>
<td>0.1</td>
<td></td>
<td></td>
<td>Ω</td>
</tr>
<tr>
<td>SHUTDOWN CONTROL</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Input Voltage High</td>
<td>$V_H$</td>
<td>$I_{SY} &lt; 100 \text{ mA}$</td>
<td>3.0</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>Input Voltage Low</td>
<td>$V_L$</td>
<td>$I_{SY} = \text{normal}$</td>
<td></td>
<td>1.3</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>POWER SUPPLY</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Power Supply Rejection Ratio</td>
<td>PSRR</td>
<td>$V_S = 4.75 \text{ V to 5.25 V}$</td>
<td>66</td>
<td></td>
<td></td>
<td>dB</td>
</tr>
<tr>
<td>Supply Current</td>
<td>$I_{SY}$</td>
<td>$V_{OUTA} = V_{OUTB} = 2.5 \text{ V}, -40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$</td>
<td>9.5</td>
<td>20</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>Supply Current, Shutdown Mode</td>
<td>$I_{SD}$</td>
<td>Pin 1 = $V_{DD}$ (see Figure 32), $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$</td>
<td>0.1</td>
<td></td>
<td></td>
<td>μA</td>
</tr>
<tr>
<td>DYNAMIC PERFORMANCE</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Gain Bandwidth Product</td>
<td>GBP</td>
<td></td>
<td>4</td>
<td></td>
<td></td>
<td>MHz</td>
</tr>
<tr>
<td>Phase Margin</td>
<td>$\Phi_M$</td>
<td></td>
<td>86</td>
<td></td>
<td></td>
<td>Degrees</td>
</tr>
<tr>
<td>AUDIO PERFORMANCE</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Total Harmonic Distortion</td>
<td>THD + N</td>
<td>$P = 0.5 \text{ W into 8 \Omega, f = 1 kHz}$</td>
<td>0.15</td>
<td></td>
<td></td>
<td>%</td>
</tr>
<tr>
<td>Total Harmonic Distortion</td>
<td>THD + N</td>
<td>$P = 1.0 \text{ W into 8 \Omega, f = 1 kHz}$</td>
<td>0.2</td>
<td></td>
<td></td>
<td>%</td>
</tr>
<tr>
<td>Voltage Noise Density</td>
<td>$e_n$</td>
<td>$f = 1 \text{ kHz}$</td>
<td>85</td>
<td></td>
<td></td>
<td>nV/√Hz</td>
</tr>
</tbody>
</table>

$V_{DD} = 3.3 \text{ V}, T_A = 25^\circ\text{C}, R_L = 8 \\Omega, C_B = 0.1 \mu\text{F}, V_{CM} = V_{DD}/2$, unless otherwise noted.

**Table 2.**

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Symbol</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>GENERAL CHARACTERISTICS</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Differential Output Offset Voltage</td>
<td>$V_{OOS}$</td>
<td>$A_{VD} = 2, -40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$</td>
<td>5</td>
<td>50</td>
<td></td>
<td>mV</td>
</tr>
<tr>
<td>Output Impedance</td>
<td>$Z_{OUT}$</td>
<td></td>
<td>0.1</td>
<td></td>
<td></td>
<td>Ω</td>
</tr>
<tr>
<td>SHUTDOWN CONTROL</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Input Voltage High</td>
<td>$V_H$</td>
<td>$I_{SY} &lt; 100 \mu\text{A}$</td>
<td>1.7</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>Input Voltage Low</td>
<td>$V_L$</td>
<td>$I_{SY} = \text{normal}$</td>
<td></td>
<td>1</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>POWER SUPPLY</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Supply Current</td>
<td>$I_{SY}$</td>
<td>$V_{OUTA} = V_{OUTB} = 1.65 \text{ V, -40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}}$</td>
<td>5.2</td>
<td>20</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>Supply Current, Shutdown Mode</td>
<td>$I_{SD}$</td>
<td>Pin 1 = $V_{DD}$ (see Figure 32), $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$</td>
<td>0.1</td>
<td></td>
<td></td>
<td>μA</td>
</tr>
<tr>
<td>AUDIO PERFORMANCE</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Total Harmonic Distortion</td>
<td>THD + N</td>
<td>$P = 0.35 \text{ W into 8 \Omega, f = 1 kHz}$</td>
<td>0.1</td>
<td></td>
<td></td>
<td>%</td>
</tr>
</tbody>
</table>
V_{DD} = 2.7 V, T_{A} = 25°C, R_{L} = 8 Ω, C_{B} = 0.1 μF, V_{CM} = V_{DD}/2, unless otherwise noted.

Table 3.

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Symbol</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>GENERAL CHARACTERISTICS</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Differential Output Offset Voltage</td>
<td>V_{OOS}</td>
<td>A_{V} = 2</td>
<td>5</td>
<td>50</td>
<td>0.1</td>
<td>mV</td>
</tr>
<tr>
<td>Output Impedance</td>
<td>Z_{OUT}</td>
<td></td>
<td>0.1</td>
<td></td>
<td></td>
<td>Ω</td>
</tr>
<tr>
<td>SHUTDOWN CONTROL</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Input Voltage High</td>
<td>V_{IH}</td>
<td>ISY = &lt;100 mA</td>
<td>1.5</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>Input Voltage Low</td>
<td>V_{IL}</td>
<td>ISY = normal</td>
<td>0.8</td>
<td></td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>POWER SUPPLY</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Supply Current</td>
<td>ISY</td>
<td>V_{OUTA} = V_{OUTB} = 1.35 V, −40°C ≤ T_{A} ≤ +85°C</td>
<td>4.2</td>
<td>20</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>Supply Current, Shutdown Mode</td>
<td>ISD</td>
<td>Pin 1 = V_{DD} (see Figure 32), −40°C ≤ T_{A} ≤ +85°C</td>
<td>0.1</td>
<td>1</td>
<td></td>
<td>μA</td>
</tr>
<tr>
<td>AUDIO PERFORMANCE</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Total Harmonic Distortion</td>
<td>THD + N</td>
<td>P = 0.25 W into 8 Ω, f = 1 kHz</td>
<td>0.1</td>
<td></td>
<td></td>
<td>%</td>
</tr>
</tbody>
</table>
ABSOLUTE MAXIMUM RATINGS

Absolute maximum ratings apply at $T_a = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Rating</th>
</tr>
</thead>
<tbody>
<tr>
<td>Supply Voltage</td>
<td>6 V</td>
</tr>
<tr>
<td>Input Voltage $V_{DD}$</td>
<td>$V_{DD}$</td>
</tr>
<tr>
<td>Common-Mode Input Voltage</td>
<td>2000 V</td>
</tr>
<tr>
<td>ESD Susceptibility</td>
<td>2000 V</td>
</tr>
<tr>
<td>Storage Temperature Range</td>
<td>$-65^\circ\text{C}$ to $+150^\circ\text{C}$</td>
</tr>
<tr>
<td>Operating Temperature Range</td>
<td>$-40^\circ\text{C}$ to $+85^\circ\text{C}$</td>
</tr>
<tr>
<td>Junction Temperature Range</td>
<td>$-65^\circ\text{C}$ to $+165^\circ\text{C}$</td>
</tr>
<tr>
<td>Lead Temperature, Soldering (60 sec)</td>
<td>300°C</td>
</tr>
</tbody>
</table>

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

$\theta_{JA}$ is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 5. Thermal Resistance

<table>
<thead>
<tr>
<th>Package Type</th>
<th>$\theta_{JA}$</th>
<th>$\theta_{JC}$</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>8-Lead LFCSP⁰ VD (CP-Suffix)¹</td>
<td>50</td>
<td>75</td>
<td>°C/W</td>
</tr>
<tr>
<td>8-Lead SOIC N (S-Suffix)²</td>
<td>121</td>
<td>43</td>
<td>°C/W</td>
</tr>
</tbody>
</table>

¹ For the LFCSP VD, $\theta_{JA}$ is measured with exposed lead frame soldered to the PCB.
² For the SOIC N, $\theta_{JA}$ is measured with the device soldered to a four-layer PCB.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.
PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

Table 6. Pin Function Descriptions

<table>
<thead>
<tr>
<th>Pin No.</th>
<th>Mnemonic</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>SHUTDOWN</td>
<td>Shutdown Enable.</td>
</tr>
<tr>
<td>2</td>
<td>BYPASS</td>
<td>Bypass Capacitor.</td>
</tr>
<tr>
<td>3</td>
<td>IN+</td>
<td>Noninverting Input.</td>
</tr>
<tr>
<td>4</td>
<td>IN−</td>
<td>Inverting Input.</td>
</tr>
<tr>
<td>5</td>
<td>V_OUTA</td>
<td>Output A.</td>
</tr>
<tr>
<td>6</td>
<td>V+</td>
<td>Positive Supply.</td>
</tr>
<tr>
<td>7</td>
<td>V−</td>
<td>Negative Supply.</td>
</tr>
<tr>
<td>8</td>
<td>V_OUTB</td>
<td>Output B.</td>
</tr>
<tr>
<td></td>
<td>EPAD</td>
<td>Exposed Pad. Connect the exposed pad to V−.</td>
</tr>
</tbody>
</table>
TYPICAL PERFORMANCE CHARACTERISTICS

Figure 4. THD + N vs. Frequency

Figure 5. THD + N vs. Frequency

Figure 6. THD + N vs. Frequency

Figure 7. THD + N vs. Frequency

Figure 8. THD + N vs. Frequency

Figure 9. THD + N vs. Frequency
Table: THD + N vs. POUT

<table>
<thead>
<tr>
<th>THD + N (%)</th>
<th>POUT (W)</th>
</tr>
</thead>
<tbody>
<tr>
<td>0.01</td>
<td>0.1</td>
</tr>
<tr>
<td>0.1</td>
<td>1</td>
</tr>
</tbody>
</table>

Note: TA = 25°C, VDD = 5V, AVD = 2 (BTL), RL = 8Ω, FREQUENCY = 20Hz, CB ≈ 0.1 µF

Figure 10. THD + N vs. POUT

Figure 11. THD + N vs. POUT

Figure 12. THD + N vs. POUT

Figure 13. THD + N vs. Frequency

Figure 14. THD + N vs. Frequency

Figure 15. THD + N vs. Frequency
Figure 16. THD + N vs. P_OUTPUT

Figure 17. THD + N vs. P_OUTPUT

Figure 18. THD + N vs. P_OUTPUT

Figure 19. THD + N vs. Frequency

Figure 20. THD + N vs. Frequency

Figure 21. THD + N vs. Frequency
Figure 22. THD + N vs. P<sub>OUTPUT</sub>

Figure 23. THD + N vs. P<sub>OUTPUT</sub>

Figure 24. THD + N vs. P<sub>OUTPUT</sub>

Figure 25. THD + N vs. Frequency

Figure 26. THD + N vs. Frequency

Figure 27. THD + N vs. Frequency
LOAD RESISTANCE (Ω)

OUTPUT POWER (W)

1.6
0.6
0
4 8 12 16 20 24 28 32 36 40 44 48

0.4
0.2
0.8
0.4
0.2
1.2
1.0
5V
3.3V
2.7V

Figure 34. P_{\text{output}} vs. Load Resistance

OUTPUT OFFSET VOLTAGE (mV)

NUMBER OF UNITS

25
20
15
10
5
0
10
15
20
25

20
16
12
8
4

V_{\text{DD}} = 2.7V
SAMPLE SIZE = 300

V_{\text{DD}} = 3.3V
SAMPLE SIZE = 300

Figure 36. Output Offset Voltage Distribution

Figure 37. Output Offset Voltage Distribution

GAIN (dB)

PHASE SHIFT (Degrees)

80
60
40
20
0
–20
–40
–60
–80
–100

100 1k 10k 100k 1M 10M

180
135
90
45
0
–45
–90
–135

00358-036

Figure 35. Gain and Phase Shift vs. Frequency (Single Amplifier)
OUTPUT OFFSET VOLTAGE (mV)

-30 -20 -10 0 10 20 30

V \text{DD} = 3.3V
SAMPLE SIZE = 300

V \text{DD} = 5V
SAMPLE SIZE = 1,700

SUPPLY CURRENT (mA)

6 7 8 9 10 11 12 13 14 15

FREQUENCY (Hz)

PSRR (dB)

-70 -65 -60 -55 -50

TA = 25°C
V \text{DD} = 5V ± 100mV
C_B = 15\mu F
A_{\text{VOP}} = 2

Figure 38. Output Offset Voltage Distribution

Figure 39. Supply Current Distribution

Figure 40. PSRR vs. Frequency
**PRODUCT OVERVIEW**

The SSM2211 is a low distortion speaker amplifier that can run from a 2.7 V to 5.5 V supply. It consists of a rail-to-rail input and a differential output that can be driven within 400 mV of either supply rail while supplying a sustained output current of 350 mA. The SSM2211 is unity-gain stable, requiring no external compensation capacitors, and can be configured for gains of up to 40 dB. Figure 41 shows the simplified schematic.

Pin 4 and Pin 3 are the inverting and noninverting terminals to A1. An offset voltage is provided at Pin 2, which should be connected to Pin 3 for use in single-supply applications. The output of A1 appears at Pin 5. A second operational amplifier, A2, is configured with a fixed gain of $A_V = -1$ and produces an inverted replica of Pin 5 at Pin 8. The SSM2211 outputs at Pin 5 and Pin 8 produce a bridged configuration output to which a speaker can be connected. This bridge configuration offers the advantage of a more efficient power transfer from the input to the speaker. Because both outputs are symmetric, the dc bias at Pin 5 and Pin 8 are exactly equal, resulting in zero dc differential voltage across the outputs. This eliminates the need for a coupling capacitor at the output.

**THERMAL PERFORMANCE—LFCSP**

The LFCSP offers the SSM2211 user even greater choices when considering thermal performance criteria. For the 8-lead, 3 mm × 3 mm LFCSP, the $\theta_{JA}$ is 50°C/W. This is a significant performance improvement over most other packaging options.
TYPICAL APPLICATIONS

Figure 42 shows how the SSM2211 is connected in a typical application. The SSM2211 can be configured for gain much like a standard operational amplifier. The gain from the audio input to the speaker is

$$A_v = 2 \times \frac{R_F}{R_I} \quad (1)$$

The 2× factor results from Pin 8 having an opposite polarity of Pin 5, providing twice the voltage swing to the speaker from the bridged-output (BTL) configuration.

CS is a supply bypass capacitor used to provide power supply filtering. Pin 2 is connected to Pin 3 to provide an offset voltage for single-supply use, with CB providing a low ac impedance to ground to enhance power-supply rejection. Because Pin 4 is a virtual ac ground, the input impedance is equal to RI. CC is the input coupling capacitor, which also creates a high-pass filter with a corner frequency of

$$f_{HP} = \frac{1}{2\pi R_L \times C_C} \quad (2)$$

Because the SSM2211 has an excellent phase margin, a feedback capacitor in parallel with Rf to band limit the amplifier is not required, as it is in some competitor products.

BRIDGED OUTPUT VS. SINGLE-ENDED OUTPUT CONFIGURATIONS

The power delivered to a load with a sinusoidal signal can be expressed in terms of the peak voltage of the signal and the resistance of the load as

$$P_L = \frac{V_{PK}^2}{2 \times R_L} \quad (3)$$

By driving a load from a BTL configuration, the voltage swing across the load doubles. Therefore, an advantage in using a BTL configuration becomes apparent from Equation 3, as doubling the peak voltage results in four times the power delivered to the load. In a typical application operating from a 5 V supply, the maximum power that can be delivered by the SSM2211 to an 8 Ω speaker in a single-ended configuration is 250 mW. By driving this speaker with a bridged output, 1 W of power can be delivered. This translates to a 12 dB increase in sound pressure level from the speaker.

Driving a speaker differentially from a BTL offers another advantage in that it eliminates the need for an output coupling capacitor to the load. In a single-supply application, the quiescent voltage at the output is half of the supply voltage. If a speaker is connected in a single-ended configuration, a coupling capacitor is needed to prevent dc current from flowing through the speaker. This capacitor also needs to be large enough to prevent low frequency roll-off. The corner frequency is given by

$$f_{-3dB} = \frac{1}{2\pi R_L \times C_C} \quad (4)$$

where RL is the speaker resistance and CC is the coupling capacitance.

For an 8 Ω speaker and a corner frequency of 20 Hz, a 1000 µF capacitor is needed, which is physically large and costly. By connecting a speaker in a BTL configuration, the quiescent differential voltage across the speaker becomes nearly zero, eliminating the need for the coupling capacitor.

SPEAKER EFFICIENCY AND LOUDNESS

The effective loudness of 1 W of power delivered into an 8 Ω speaker is a function of speaker efficiency. The efficiency is typically rated as the sound pressure level (SPL) at 1 meter in front of the speaker with 1 W of power applied to the speaker. Most speakers are between 85 dB and 95 dB SPL at 1 meter at 1 W. Table 7 shows a comparison of the relative loudness of different sounds.

<table>
<thead>
<tr>
<th>Source of Sound</th>
<th>SPL (dB)</th>
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</thead>
<tbody>
<tr>
<td>Threshold of Pain</td>
<td>120</td>
</tr>
<tr>
<td>Heavy Street Traffic</td>
<td>95</td>
</tr>
<tr>
<td>Cabin of Jet Aircraft</td>
<td>80</td>
</tr>
<tr>
<td>Average Conversation</td>
<td>65</td>
</tr>
<tr>
<td>Average Home at Night</td>
<td>50</td>
</tr>
<tr>
<td>Quiet Recording Studio</td>
<td>30</td>
</tr>
<tr>
<td>Threshold of Hearing</td>
<td>0</td>
</tr>
</tbody>
</table>

Consequently, Table 7 demonstrates that 1 W of power into a speaker can produce quite a bit of acoustic energy.
POWER DISSIPATION

Another important advantage in using a BTL configuration is the fact that bridged-output amplifiers are more efficient than single-ended amplifiers in delivering power to a load. Efficiency is defined as the ratio of the power from the power supply to the power delivered to the load

$$\eta = \frac{P_S}{P_{SV}}$$

An amplifier with a higher efficiency has less internal power dissipation, which results in a lower die-to-case junction temperature compared with an amplifier that is less efficient. This is important when considering the amplifier maximum power dissipation rating vs. ambient temperature. An internal power dissipation vs. output power equation can be derived to fully understand this.

The internal power dissipation of the amplifier is the internal voltage drop multiplied by the average value of the supply current. An easier way to find internal power dissipation is to measure the difference between the power delivered by the supply voltage source and the power delivered into the load. The waveform of the supply current for a bridged-output amplifier is shown in Figure 43.

$$P_{DISS} = Vdd \times \frac{2}{\pi R_L} \times \frac{V_{peak}}{\pi R_L}$$

The power dissipated internally by the amplifier is simply the difference between Equation 6 and Equation 3. The equation for internal power dissipated, \(P_{DISS}\), expressed in terms of power delivered to the load and load resistance, is

$$P_{DISS} = \frac{2 \sqrt{2} V_{dd}}{\pi \sqrt{R_L}} \times \frac{1}{\sqrt{P_L}} \times P_L - P_L$$

The graph of this equation is shown in Figure 44.

Because the efficiency of a bridged-output amplifier (Equation 3 divided by Equation 6) increases with the square root of \(P_L\), the power dissipated internally by the device stays relatively flat and actually decreases with higher output power. The maximum power dissipation of the device can be found by differentiating Equation 7 with respect to load power and setting the derivative equal to zero. This yields

$$\frac{\partial P_{DISS}}{\partial P_L} = \frac{2 V_{dd}}{\pi R_L} \times \frac{1}{\sqrt{P_L}} - 1 = 0$$

and occurs when

$$P_{DISS,MAX} = \frac{\frac{2 V_{dd}}{\pi R_L}}{\frac{2}{\pi R_L}}$$

Using Equation 9 and the power derating curve in Figure 31, the maximum ambient temperature can be found easily. This ensures that the SSM2211 does not exceed its maximum junction temperature of 150°C. The power dissipation for a single-ended output application where the load is capacitively coupled is given by

$$P_{DISS} = \frac{2 \sqrt{2} V_{dd}}{\pi \sqrt{R_L}} \times \frac{1}{\sqrt{P_L}} \times P_L$$

The graph of Equation 10 is shown in Figure 45.
The maximum power dissipation for a single-ended output is

$$P_{\text{Diss, Max}} = \frac{V_{\text{DD}}^2}{2\pi R_L}$$

(11)

**OUTPUT VOLTAGE HEADROOM**

The outputs of both amplifiers in the SSM2211 can come within 400 mV of either supply rail while driving an 8 Ω load. As compared with equivalent competitor products, the SSM2211 has a higher output voltage headroom. This means that the SSM2211 can deliver an equivalent maximum output power while running from a lower supply voltage. By running at a lower supply voltage, the internal power dissipation of the device is reduced, as shown in Equation 9. This extended output headroom, along with the LFCSP, allows the SSM2211 to operate in higher ambient temperatures than competitor devices.

The SSM2211 is also capable of providing amplification even at supply voltages as low as 2.7 V. The maximum power available at the output is a function of the supply voltage. Therefore, as the supply voltage decreases, so does the maximum power output from the device. The maximum output power vs. supply voltage at various BTL resistances is shown in Figure 46. The maximum output power is defined as the point at which the output has 1% total harmonic distortion (THD + N).

To find the minimum supply voltage needed to achieve a specified maximum undistorted output power use Figure 46. For example, an application requires only 500 mW to be output for an 8 Ω speaker. With the speaker connected in a bridged-output configuration, the minimum supply voltage required is 3.3 V.

The SSM2211 can be put into a low power consumption shutdown mode by connecting Pin 1 to 5 V. In shutdown mode, the SSM2211 has an extremely low supply current of less than 10 nA. This makes the SSM2211 ideal for battery-powered applications.

Connect Pin 1 to ground for normal operation. Connecting Pin 1 to VDD mutes the outputs and puts the device into shutdown mode. A pull-up or pull-down resistor is not required. Pin 1 should always be connected to a fixed potential, either VDD or ground, and never be left floating. Leaving Pin 1 unconnected can produce unpredictable results.

**AUTOMATIC SHUTDOWN-SENSING CIRCUIT**

Figure 47 shows a circuit that can be used to take the SSM2211 in and out of shutdown mode automatically. This circuit can be set to turn the SSM2211 on when an input signal of a certain amplitude is detected. The circuit also puts the device into low power shutdown mode if an input signal is not sensed within a certain amount of time. This can be useful in a variety of portable radio applications, where power conservation is critical.
The input signal to the SSM2211 is also connected to the non-inverting terminal of A2. R1, R2, and R3 set the threshold voltage at which the SSM2211 is to be taken out of shutdown mode. The diode, D1, half-wave rectifies the output of A2, discharging C1 to ground when an input signal greater than the set threshold voltage is detected. R4 controls the charge time of C1, which sets the time until the SSM2211 is put back into shutdown mode after the input signal is no longer detected.

R5 and R6 are used to establish a voltage reference point equal to half of the supply voltage. R7 and R8 set the gain of the SSM2211. A 1N914 or equivalent diode is required for D1, and A2 must be a rail-to-rail output amplifier, such as AD8500 or equivalent. This ensures that C1 discharges sufficiently to bring the SSM2211 out of shutdown mode.

To find the appropriate component values, the gain of A2 must be determined by

\[ A_v = \frac{V_{ST}}{V_{THS}} \]

where:
- \( V_{ST} \) is the single supply voltage.
- \( V_{THS} \) is the threshold voltage.
- \( A_v \) must be set to a minimum of 2 for the circuit to work properly.

Next, choose R1 and set R2 to

\[ R_2 = R_1 \left(1 - \frac{2}{A_v}\right) \]

Find R3 as

\[ R_3 = \frac{R_1 \times R_2}{R_2 + R_2} \times (A_v - 1) \]

C1 can be arbitrarily set but should be small enough to prevent A2 from becoming capacitively overloaded. R4 and C1 control the shutdown rate. To prevent intermittent shutdown with low frequency input signals, the minimum time constant must be

\[ R_4 \times C_1 \geq \frac{10}{f_{LOW}} \]

where \( f_{LOW} \) is the lowest input frequency expected.

### SHUTDOWN-CIRCUIT DESIGN EXAMPLE

In this example, a portable radio application requires the SSM2211 to be turned on when an input signal greater than 50 mV is detected. The device needs to return to shutdown mode within 500 ms after the input signal is no longer detected. The lowest frequency of interest is 200 Hz, and a 5 V supply is used.

The minimum gain of the shutdown circuit, from Equation 12, is \( A_v = 100 \). R1 is set to 100 kΩ. Using Equation 13 and Equation 14, R2 = 98 kΩ and R3 = 4.9 MΩ. C1 is set to 0.01 µF, and based on Equation 15, R4 is set to 10 MΩ. To minimize power supply current, R5 and R6 are set to 10 MΩ. The previous procedure provides an adequate starting point for the shutdown circuit. Some component values may need to be adjusted empirically to optimize performance.

### START-UP POPPING NOISE

During power-up or release from shutdown mode, the midrail bypass capacitor, \( C_b \), determines the rate at which the SSM2211 starts up. By adjusting the charging time constant of \( C_b \), the start-up pop noise can be pushed into the subaudible range, greatly reducing start-up popping noise. On power-up, the midrail bypass capacitor is charged through an effective resistance of 25 kΩ. To minimize start-up popping, the charging time constant for \( C_b \) needs to be greater than the charging time constant for the input coupling capacitor, \( C_c \).

\[ C_b \times 25 \text{ kΩ} > C_c \times R_1 \]

For an application where \( R_1 = 10 \text{ kΩ} \) and \( C_c = 0.22 \mu \text{F} \), \( C_b \) must be at least 0.1 µF to minimize start-up popping noise.

### SSM2211 Amplifier Design Example

- **Maximum output power:** 1 W
- **Input impedance:** 20 kΩ
- **Load impedance:** 8 Ω
- **Input level:** 1 V rms
- **Bandwidth:** 20 Hz − 20 kHz ± 0.25 dB

The configuration shown in Figure 42 is used. The first thing to determine is the minimum supply rail necessary to obtain the specified maximum output power. From Figure 46, for 1 W of output power into an 8 Ω load, the supply voltage must be at least 4.6 V. A supply rail of 5 V can be easily obtained from a
voltage reference. The extra supply voltage also allows the SSM2211 to reproduce peaks in excess of 1 W without clipping the signal. With $V_{DD} = 5 \text{ V}$ and $R_L = 8 \Omega$, Equation 9 shows that the maximum power dissipation for the SSM2211 is 633 mW. From the power derating curve in Figure 31, the ambient temperature must be less than 50°C for the SOIC and 121°C for the LFCSP.

The required gain of the amplifier can be determined from Equation 17 as

$$A_V = \frac{V_{IN, \text{rms}}}{P_L} = 2.8$$  \hspace{1cm} (17)

From Equation 1

$$\frac{R_F}{R_1} = \frac{A_V}{2}$$

or $R_0 = 1.4 \times R_1$. Because the desired input impedance is 20 kΩ, $R_1 = 20 \text{ kΩ}$ and $R_2 = 28 \text{ kΩ}$.

The final design step is to select the input capacitor. When adding an input capacitor, $C_C$, to create a high-pass filter, the corner frequency needs to be far enough away for the design to meet the bandwidth criteria. For a first-order filter to achieve a pass-band response within 0.25 dB, the corner frequency must be at least $4.14 \times$ away from the pass-band frequency. Therefore, $(4.14 \times \text{f}_{\text{HP}}) < 20 \text{ Hz}$. Using Equation 2, the minimum size of an input capacitor can be found.

$$C_C > \frac{1}{2\pi \times 20 \text{ kΩ} \times \left(\frac{20 \text{ Hz}}{4.14}\right)}$$

(18)

Therefore, $C_C > 1.65 \text{ µF}$. Using a 2.2 µF is a practical choice for $C_C$.

The gain bandwidth product for each internal amplifier in the SSM2211 is 4 MHz. Because 4 MHz is much greater than $4.14 \times 20 \text{ kHz}$, the design meets the upper frequency bandwidth criteria. The SSM2211 can also be configured for higher differential gains without running into bandwidth limitations. Equation 16 shows an appropriate value for $C_B$ to reduce start-up popping noise.

$$C_B > \frac{(2.2 \text{ µF})(20 \text{ kΩ})}{25 \text{ kΩ}} = 1.76 \text{ µF}$$

(19)

Selecting $C_B$ to be 2.2 µF for a practical value of capacitor minimizes start-up popping noise.

To summarize the final design

$V_{DD} = 5 \text{ V}$

$R_1 = 20 \text{ kΩ}$

$R_F = 28 \text{ kΩ}$

$C_C = 2.2 \text{ µF}$

$C_A = 2.2 \text{ µF}$

$T_{A, \text{MAX}} = 85°C$

**SINGLE-ENDED APPLICATIONS**

There are applications in which driving a speaker differentially is not practical, for example, a pair of stereo speakers where the negative terminal of both speakers is connected to ground. Figure 48 shows how this can be accomplished.

It is not necessary to connect a dummy load to the unused output to help stabilize the output. The 470 µF coupling capacitor creates a high-pass frequency cutoff of 42 Hz, as given in Equation 4, which is acceptable for most computer speaker applications. The overall gain for a single-ended output configuration is $A_V = R_F/R_1$, which for this example is equal to 1.

**DRIVING TWO SPEAKERS SINGLE ENDEDLY**

It is possible to drive two speakers single endedly with both outputs of the SSM2211.

Each speaker is driven by a single-ended output. The trade-off is that only 250 mW of sustained power can be put into each speaker. In addition, a coupling capacitor must be connected in series with each of the speakers to prevent large dc currents from flowing through the 8 Ω speakers. These coupling capacitors produce a high-pass filter with a corner frequency given by Equation 4. For a speaker load of 8 Ω and a coupling capacitor of 470 µF, this results in a $\sim 3 \text{ dB}$ frequency of 42 Hz. Because the power of a single-ended output is one-quarter that of a BTL, both speakers together are still half as loud ($-6 \text{ dB SPL}$) as a single speaker driven with a BTL.
The polarity of the speakers is important because each output is 180° out of phase with the other. By connecting the negative terminal of Speaker 1 to Pin 5 and the positive terminal of Speaker 2 to Pin 8, proper speaker phase can be established. The maximum power dissipation of the device, assuming both loads are equal, can be found by doubling Equation 11. If the loads are different, use Equation 11 to find the power dissipation caused by each load, and then take the sum to find the total power dissipated by the SSM2211.

**LFCSP PCB CONSIDERATIONS**

The LFCSP is a plastic encapsulated package with a copper lead frame substrate. This is a leadless package with solder lands on the bottom surface of the package, instead of conventional formed perimeter leads. A key feature that allows the user to reach the quoted $\theta_{JA}$ performance is the exposed die attach paddle (DAP) on the bottom surface of the package. When soldered to the PCB, the DAP can provide efficient conduction of heat from the die to the PCB. To achieve optimum package performance, consideration should be given to the PCB pad design for both the solder lands and the DAP. For further information, the user is directed to the Amkor Technology document, *Application Notes for Surface Mount Assembly of Amkor's MicroLead Frame (MLF) Packages*. This can be downloaded from the Amkor Technology website.
OUTLINE DIMENSIONS

Figure 50. 8-Lead Standard Small Outline Package [SOIC_N]
Narrow Body, S-Suffix
(R-8)
Dimensions shown in millimeters and (inches)

Figure 51. 8-Lead Lead Frame Chip Scale Package [LFCSP_VD]
3 mm × 3 mm Body, Very Thin, Dual Lead
(CP-8-2)
Dimensions shown in millimeters
## ORDERING GUIDE

<table>
<thead>
<tr>
<th>Model</th>
<th>Temperature Range</th>
<th>Package Description</th>
<th>Package Option</th>
<th>Branding</th>
</tr>
</thead>
<tbody>
<tr>
<td>SSM2211CPZ-REEL</td>
<td>–40°C to +85°C</td>
<td>8-Lead LFCSP_VD</td>
<td>CP-8-2</td>
<td>B5A#</td>
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<tr>
<td>SSM2211CPZ-REEL7</td>
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<td>8-Lead LFCSP_VD</td>
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1 Z = RoHS Compliant Part; # denotes RoHS compliant product may be top or bottom marked.